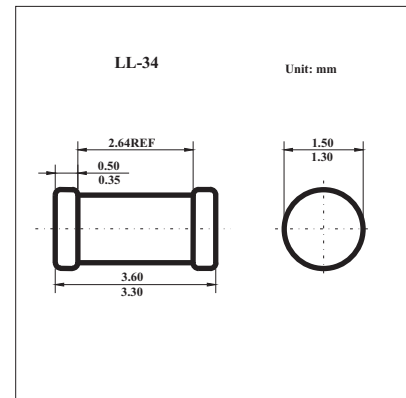


High Voltage, General Purpose Diode

KAV103(BAV103)

■ Features

- Silicon Epitaxial Planar Diodes
- For general purpose



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit	
Working Inverse Voltage	W_{iv}	200	V	
Average Rectified Current	I_o	200	mA	
DC Forward Current	I_F	500	mA	
Recurrent Peak Forward Current	i_f	600	mA	
Peak Forward Surge Current	$i_{F(surge)}$	Pulse Width = 1.0 second	1	A
		Pulse Width = 1.0 microsecond	4	
Total Power Dissipation at $T_A = 25^\circ\text{C}$	P_D	500	mW	
Linear Derating Factor from $T_A = 25^\circ\text{C}$		3.33	mW/ $^\circ\text{C}$	
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	350	$^\circ\text{C}/\text{W}$	
Operating Junction Temperature	T_J	-65 to +200	$^\circ\text{C}$	
Storage Temperature	T_{stg}	-65 to +200	$^\circ\text{C}$	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Breakdown Voltage	B_V	$I_R = 100 \mu\text{A}$	250			V
Reverse Leakage	I_R	$V_R = 200 \text{ V}$			100	nA
		$V_R = 200 \text{ V } T_A = 150^\circ\text{C}$			100	μA
Forward Voltage	V_F	$I_F = 100 \text{ mA}$			1.00	V
		$I_F = 200 \text{ mA}$			1.25	V
Capacitance	C_T	$V_R = 0.0 \text{ V}, f = 1.0 \text{ MHz}$			5.0	pF
Reverse Recovery Time	T_{RR}	$I_F = I_R = 30 \text{ mA}, I_{RR} = 1.0 \text{ mA}, R_L = 100 \Omega$			50	ns